



Electroluminescence characterization of mid-infrared InAsSb/AlInAs multi-quantum well light emitting diodes heteroepitaxially integrated on GaAs and silicon wafers

A.R Altayar^{a c}, F.A. Al-Saymari^{a d}, E. Repiso^a, L. Hanks^a, A.P. Craig^a, M. Bentley^b, E. Delli^b,
P.J. Carrington^b, A. Krier^a, A.R.J. Marshall^a  

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Highlights

- Room temperature mid-infrared electroluminescence on GaAs and Si substrates.